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CSD23201W10

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P-Channel NexFET™ Power MOSFET

Check for Samples: CSD23201W10

FEATURES

- Ultra Low Qg and Qgd
- Small Footprint 1mm x 1mm
- Low Profile 0.62mm Height
- Pb Free
- Gate ESD Protection 3kV
- RoHS Compliant
- Halogen Free

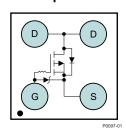
APPLICATIONS

- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

Top View



PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	-12		V
Q_g	Gate Charge Total (4.5V)	1.8		nC
Q_{gd}	Gate Charge Gate to Drain	0.26		nC
R _{DS(on)}		$V_{GS} = -1.5V$	110	mΩ
	Drain to Source On Resistance	$V_{GS} = -2.5V$	77	mΩ
		V _{GS} = -4.5V	66	mΩ
V _{GS(th)}	Threshold Voltage	-0.6		V

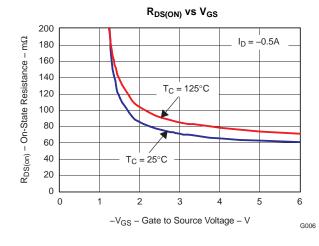
ORDERING INFORMATION

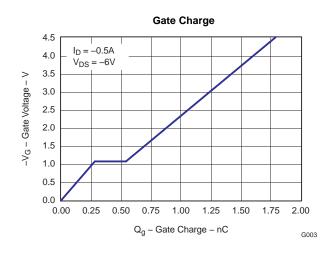
Device	Package	Media	Qty	Ship
CSD23201W10	1 x 1 Wafer Level Package	7-inch reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	-12	V
V_{GS}	V _{GS} Gate to Source Voltage -6		
I_D	Continuous Drain Current, T _C = 25°C ⁽¹⁾		Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	-8.8	Α
	Continuous Gate Clamp Current	-0.5	Α
I _G	Pulsed Gate Clamp Current	- 7	Α
P _D	Power Dissipation ⁽¹⁾	1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C

- (1) $R_{\theta JA} = 100$ °C/W on 1in^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300μs, duty cycle ≤2%







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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Static Cl	Static Characteristics						
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-12			V	
BV_{GSS}	Gate to Source Voltage;	$V_{DS} = 0V, I_{G} = -250\mu A$	-6.1		-7.2	V	
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -9.6V$			-1	μΑ	
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V$, $V_{GS} = -6V$			-100	nA	
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1.0	V	
		$V_{GS} = -1.5V, I_D = -0.5A$		110	138	mΩ	
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -0.5A$		77	96	$\text{m}\Omega$	
		$V_{GS} = -4.5V, I_D = -0.5A$		66	82	mΩ	
9 _{fs}	Transconductance	$V_{DS} = -6.0V, I_{D} = -0.5A$		9		S	
Dynamic	Characteristics						
C _{ISS}	Input Capacitance			250	325	pF	
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = -6.0V, f = 1MHz$		125	155	pF	
C _{RSS}	Reverse Transfer Capacitance			32	42	pF	
Q_g	Gate Charge Total (-4.5V)			1.8	2.4	nC	
Q_{gd}	Gate Charge Gate to Drain	$V_{DS} = -6.0V$, $I_{D} = -0.5A$		0.26		nC	
Q_{gs}	Gate Charge Gate to Source	$v_{DS} = -6.0V, i_D = -0.5A$		0.28		nC	
Q _{g(th)}	Gate Charge at Vth			0.11		nC	
Q _{OSS}	Output Charge	$V_{DS} = -6.0V, V_{GS} = 0V$		1.7		nC	
t _{d(on)}	Turn On Delay Time			24		ns	
t _r	Rise Time	$V_{DS} = -6.0V$, $V_{GS} = -2.5V$, $I_{D} = -0.5A$		19		ns	
t _{d(off)}	Turn Off Delay Time	$R_G = 20\Omega$		68		ns	
t _f	Fall Time			29		ns	
Diode C	Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_{S} = -0.5A, V_{GS} = 0V$		-0.77	-1.0	V	
Q _{rr}	Reverse Recovery Charge	V_{dd} = -4.0V, I_F = -0.5A, di/dt = 100A/ μ s		2		nC	
t _{rr}	Reverse Recovery Time	V_{dd} = -4.0V, I_F = -0.5A, di/dt = 100A/ μ s		9.5		ns	

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Ambient (Minimum Cu area)			245	°C/W
R $_{\theta JA}$	Thermal Resistance Junction to Ambient (1 in ² Cu area)			125	°C/W

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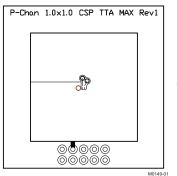
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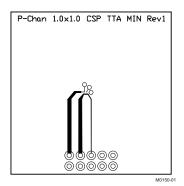
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Max $R_{\theta JA} = 125^{\circ}\text{C/W}$ when mounted on 1inch² of 2 oz. Cu.



Max $R_{\theta JA} = 245^{\circ}\text{C/W}$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

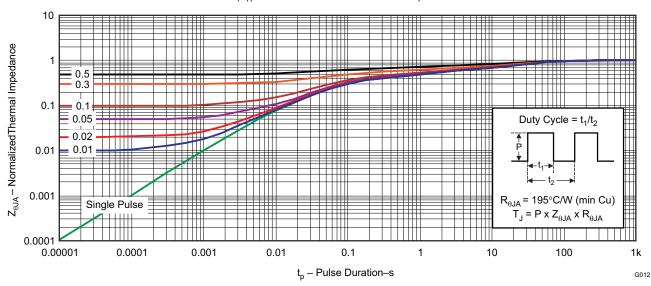


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

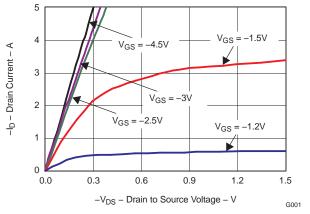


Figure 2. Saturation Characteristics

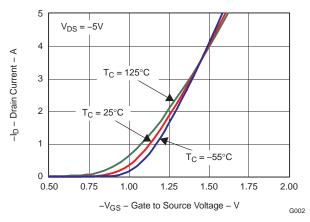


Figure 3. Transfer Characteristics

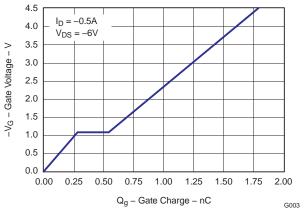


Figure 4. Gate Charge

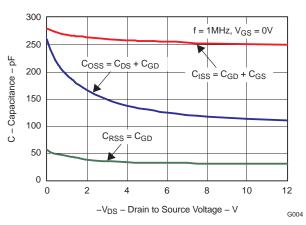


Figure 5. Capacitance

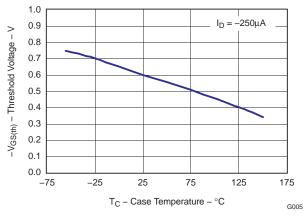


Figure 6. Threshold Voltage vs. Temperature

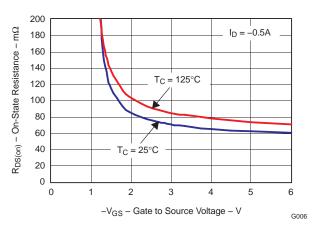


Figure 7. On Resistance vs. Gate Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

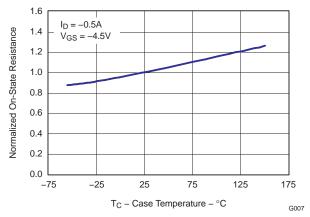


Figure 8. On Resistance vs. Temperature

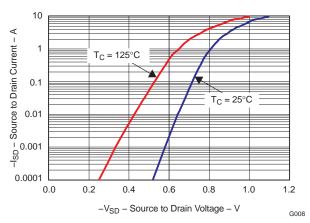


Figure 9. Typical Diode Forward Voltage

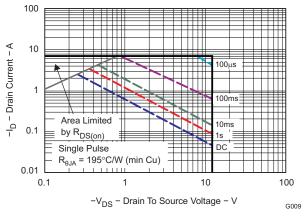


Figure 10. Maximum Safe Operating Area

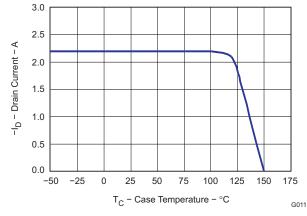


Figure 11. Maximum Drain Current vs. Temperature

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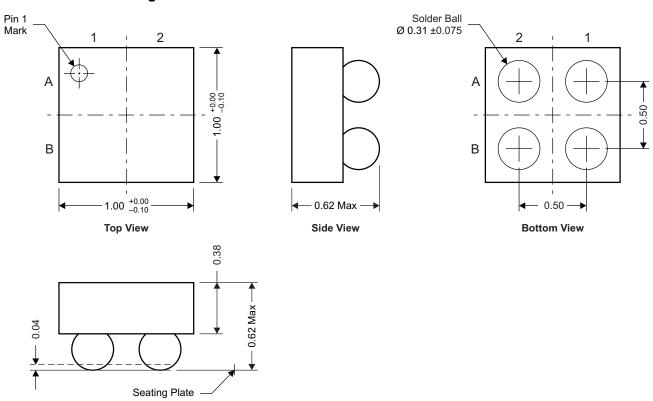
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M0151-01

MECHANICAL DATA

CSD23201W10 Package Dimensions



NOTE: All dimensions are in mm (unless otherwise specified)

Front View

Pin Configuration Table

POSITION	DESIGNATION	
B1	Source	
A1	Gate	
A2, B2	Drain	

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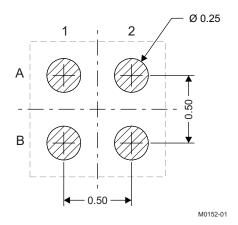


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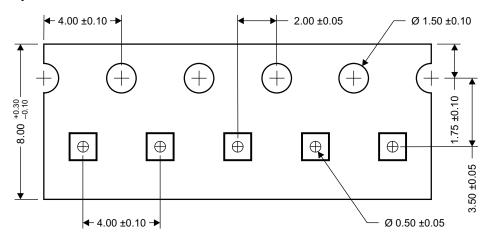
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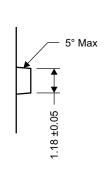
Land Pattern Recommendation

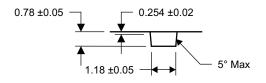


NOTE: All dimensions are in mm (unless otherwise specified)

Tape and Reel Information







M0153-01

NOTE: All dimensions are in mm (unless otherwise specified)

REVISION HISTORY

Changes from Original (August 2009) to Revision A

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